



SANYO Semiconductors

DATA SHEET

2SA1252 / 2SC3134

 — PNP / NPN Epitaxial Planar Silicon Transistors

High VEBO, AF Amp Applications

Features

- High VEBO.
- Wide ASO and high durability against breakdown.

Specifications () : 2SA1252

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		(-)60	V
Collector-to-Emitter Voltage	V _{CEO}		(-)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)15	V
Collector Current	I _C		(-)150	mA
Collector Current (Pulse)	I _{CP}		(-)300	mA
Collector Dissipation	P _C		200	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CB0}	V _{CB} =(-)40V, I _E =0A			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)10V, I _C =0A			(-)0.1	μA
DC Current Gain	h _{FE}	V _{CE} =(-)6V, I _C =(-)1mA	90*		600*	
Gain-Bandwidth Product	f _T	V _{CE} =(-)6V, I _C =(-)1mA		100		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)6V, f=1MHz		(3.5)2.2		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)50mA, I _B =(-)5mA			(-)0.5	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μA, I _E =0A	(-)60			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =(-)1mA, R _{BE} =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0A	(-)15			V

Marking: 2SA1252:D

2SC3134: H

* : The 2SA1252 / 2SC3134 are classified by 1mA h_{FE} as follows:

Rank	4	5	6	7
h _{FE}	90 to 180	135 to 270	200 to 400	300 to 600

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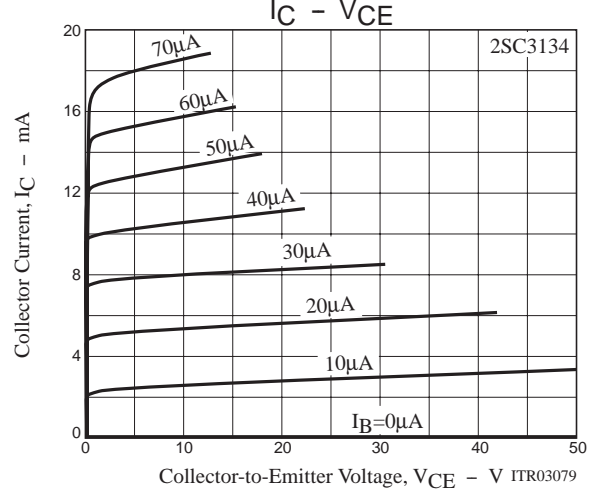
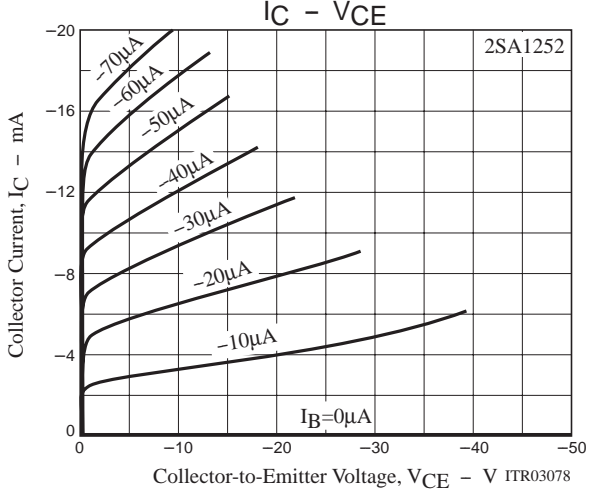
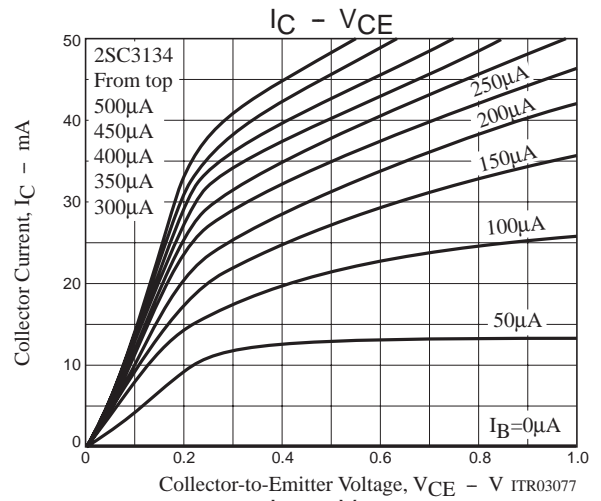
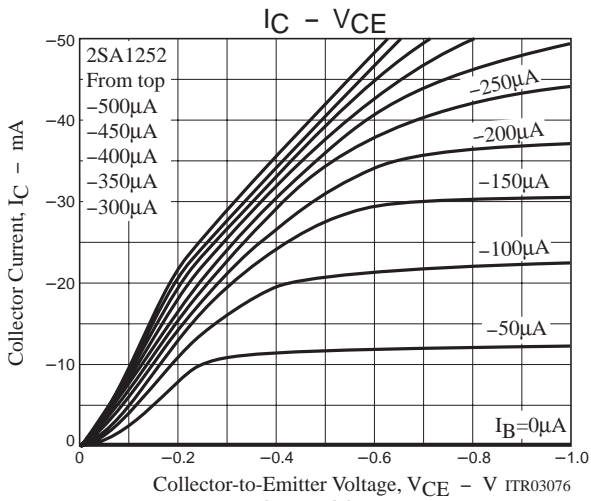
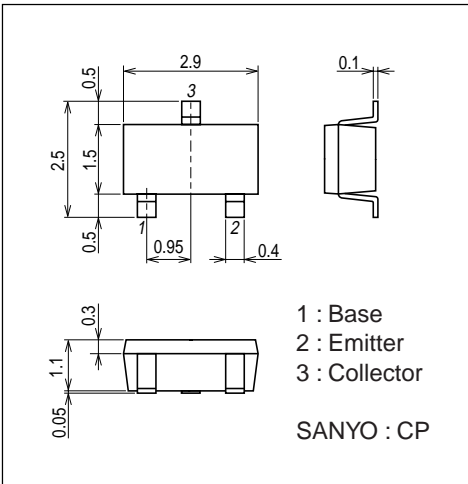
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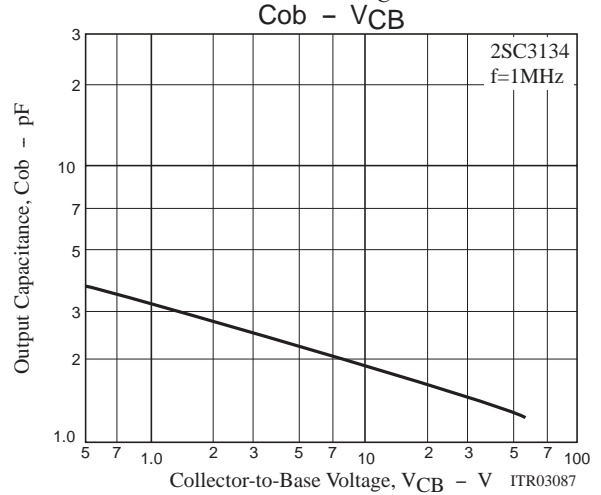
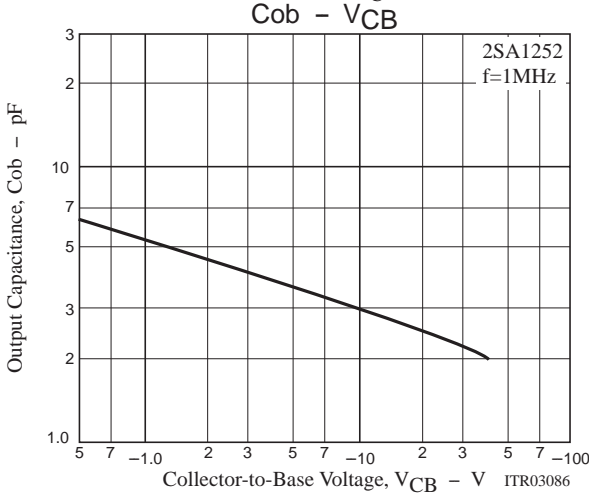
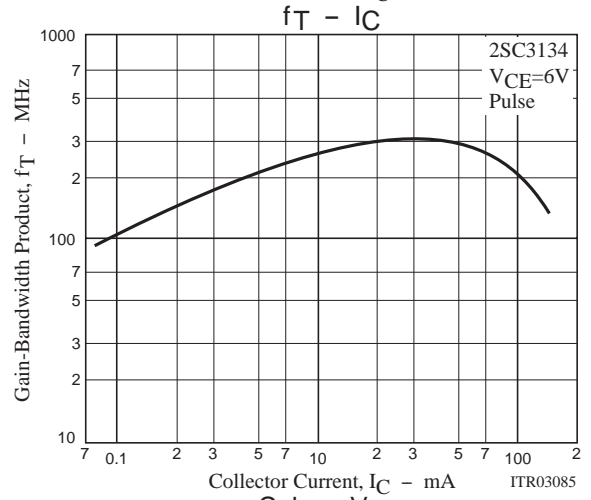
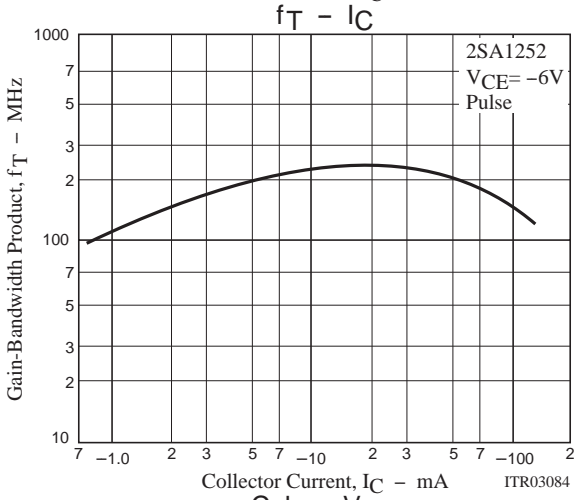
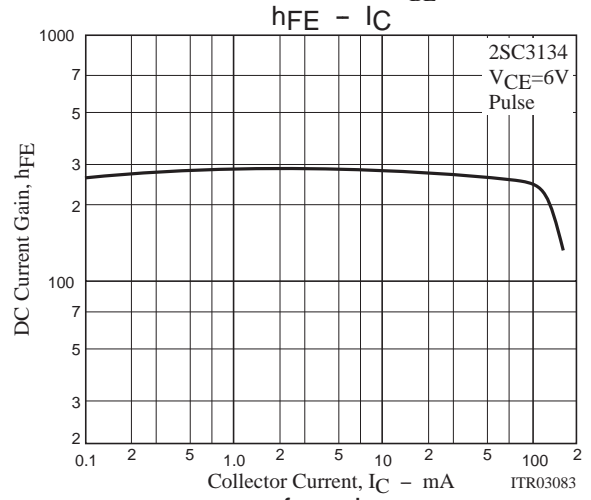
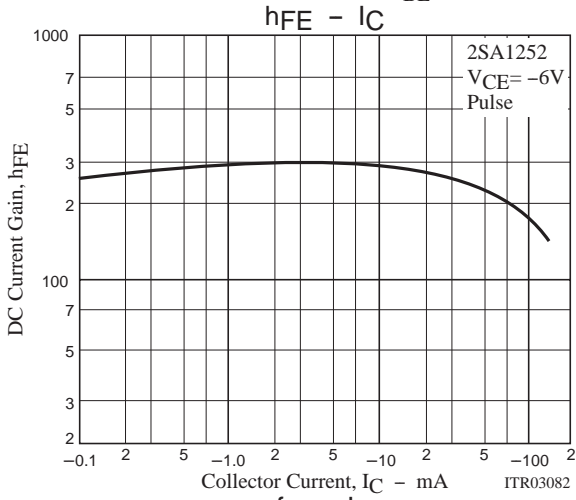
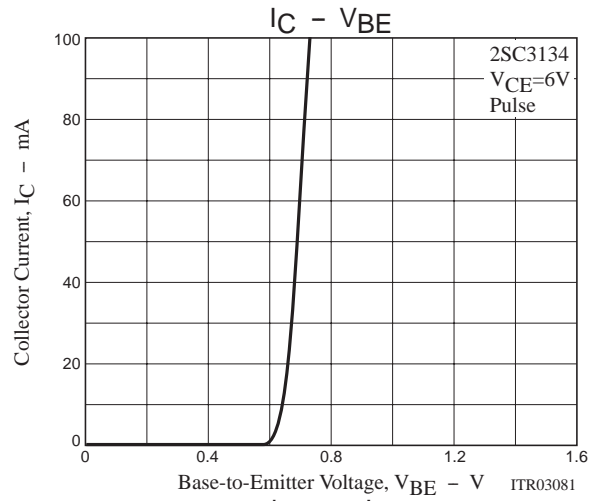
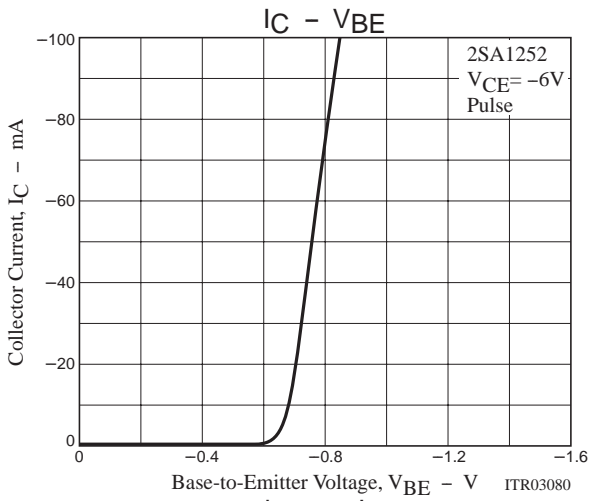
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Package Dimensions

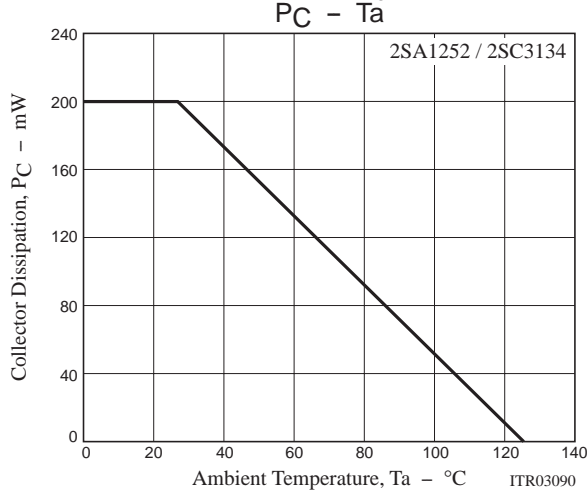
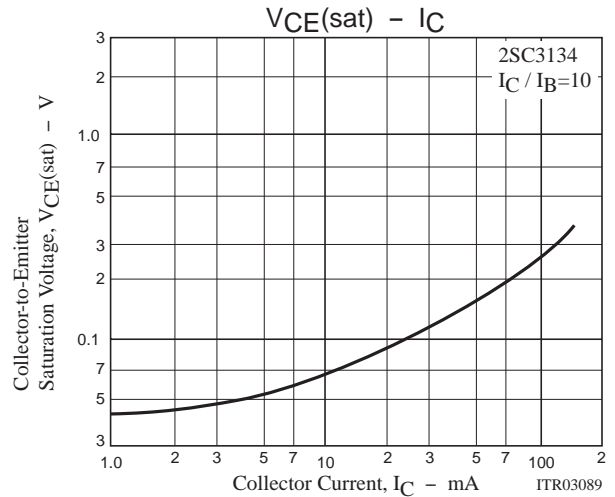
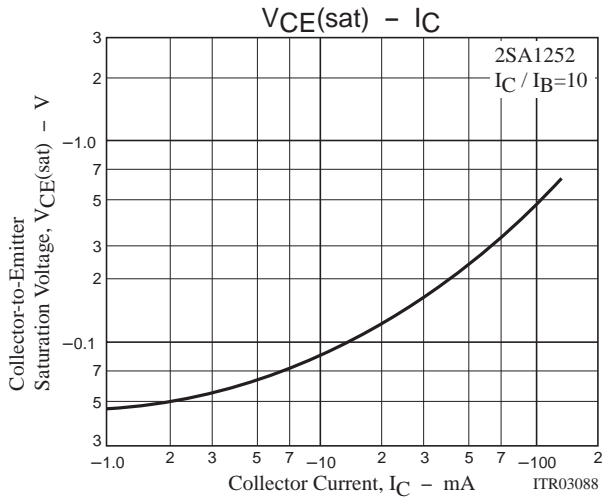
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7013A-009



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